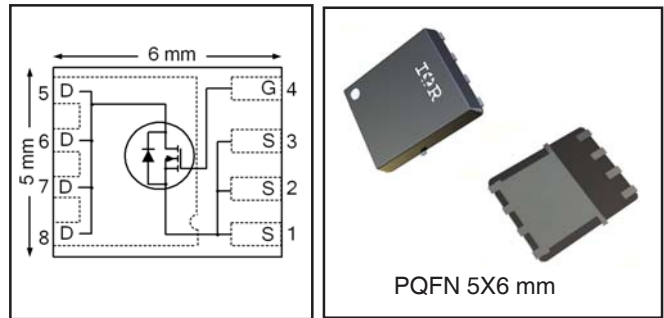


$V_{DS}$	<b>30</b>	<b>V</b>
$V_{GS\ max}$	<b>± 20</b>	<b>V</b>
$R_{DS(on)\ max}$ (@ $V_{GS} = 10V$ )	<b>2.1</b>	<b>mΩ</b>
(@ $V_{GS} = 4.5V$ )	<b>3.2</b>	
$Q_g\ typ.$	<b>30</b>	<b>nC</b>
$I_D$ (@ $T_{c(Bottom)} = 25^\circ C$ )	<b>80</b> ⑦	<b>A</b>

HEXFET® Power MOSFET



**Applications**

- Synchronous MOSFET for high frequency buck converters

**Features and Benefits**

**Features**

Low Thermal Resistance to PCB (< 1.3°C/W)
Low Profile (<1.2mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

results in  
 ⇒

**Benefits**

Enable better thermal dissipation
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base part number	Package Type	Standard Pack		Orderable part number	Note
		Form	Quantity		
IRFH8311TRPBF	PQFN 5mm x 6mm	Tape and Reel	4000	IRFH8311TRPBF	
IRFH8311TR2PBF	PQFN 5mm x 6mm	Tape and Reel	400	IRFH8311TR2PBF	EOL notice #259

**Absolute Maximum Ratings**

	Parameter	Max.	Units	
$V_{DS}$	Drain-to-Source Voltage	30	V	
$V_{GS}$	Gate-to-Source Voltage	± 20		
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	32	A	
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	26		
$I_D @ T_{c(Bottom)} = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	169 ⑦		
$I_D @ T_{c(Bottom)} = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	107 ⑦		
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited)	80 ⑦		
	$I_{DM}$	Pulsed Drain Current ①	400	
	$P_D @ T_A = 25^\circ C$	Power Dissipation ⑤	3.6	W
	$P_D @ T_{c(Bottom)} = 25^\circ C$	Power Dissipation ⑤	96	
		Linear Derating Factor ⑤	0.029	W/°C
$T_J$	Operating Junction and	-55 to + 150	°C	
$T_{STG}$	Storage Temperature Range			

Notes ① through ⑦ are on page 9

**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

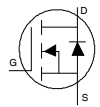
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.021	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	1.70	2.10	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A ③
		—	2.60	3.20		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 16A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.35	1.8	2.35	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 100μA
ΔV <sub>GS(th)</sub>	Gate Threshold Voltage Coefficient	—	-6.6	—	mV/°C	
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		—	—	150		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
g <sub>fs</sub>	Forward Transconductance	83	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 20A
Q <sub>g</sub>	Total Gate Charge	—	66	—	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 20A
Q <sub>g</sub>	Total Gate Charge	—	30	—	nC	V <sub>DS</sub> = 15V V <sub>GS</sub> = 4.5V I <sub>D</sub> = 20A
Q <sub>gs1</sub>	Pre-V <sub>th</sub> Gate-to-Source Charge	—	9.7	—		
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-to-Source Charge	—	3.9	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	8.6	—		
Q <sub>gqdr</sub>	Gate Charge Overdrive	—	7.8	—		
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> )	—	12.5	—		
Q <sub>oss</sub>	Output Charge	—	21	—	nC	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
R <sub>G</sub>	Gate Resistance	—	0.6	—	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	21	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 4.5V I <sub>D</sub> = 20A R <sub>G</sub> = 1.8Ω
t <sub>r</sub>	Rise Time	—	26	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	21	—		
t <sub>f</sub>	Fall Time	—	12	—		
C <sub>iss</sub>	Input Capacitance	—	4960	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 10V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	1065	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	455	—		

**Avalanche Characteristics**

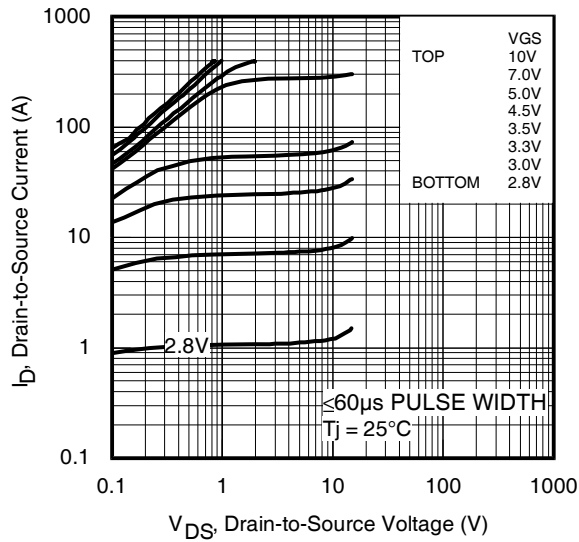
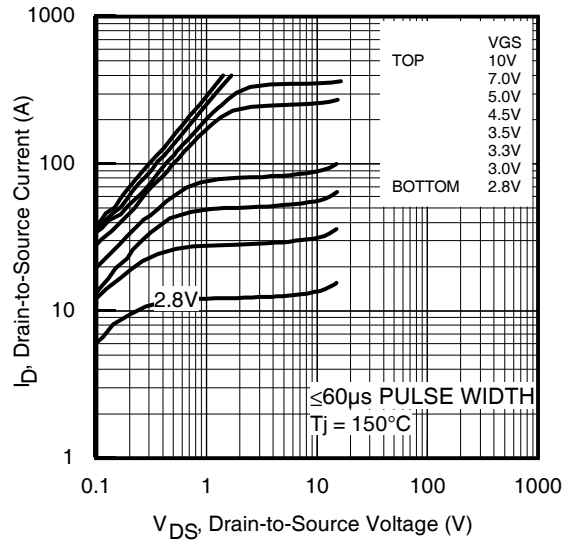
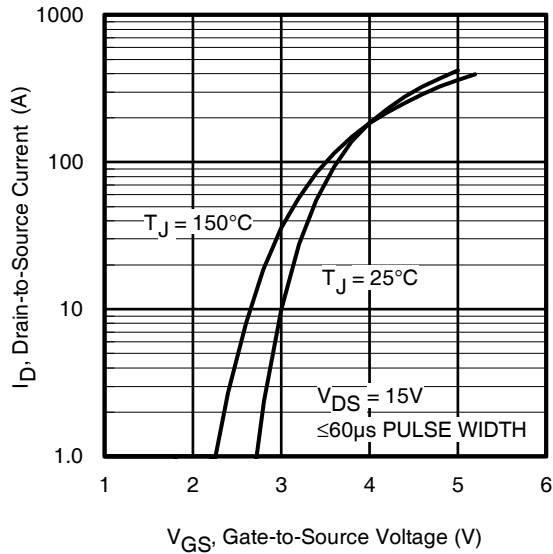
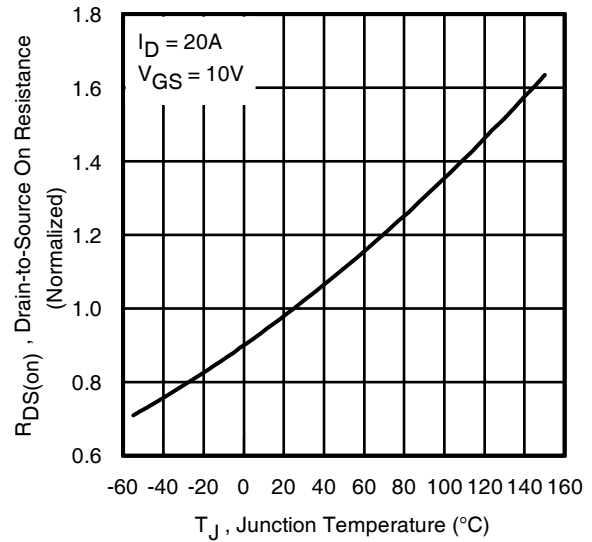
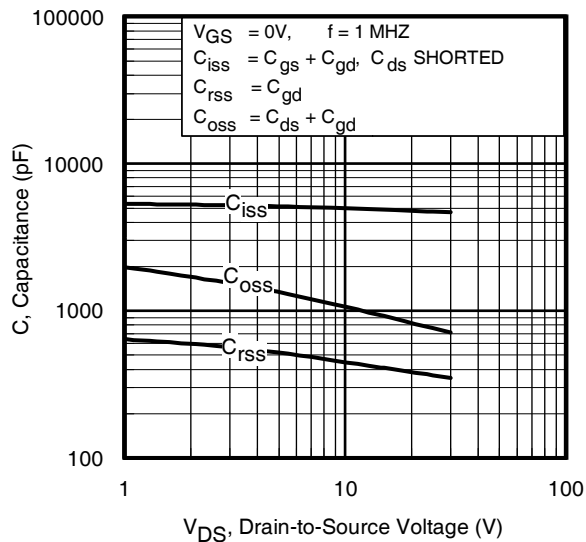
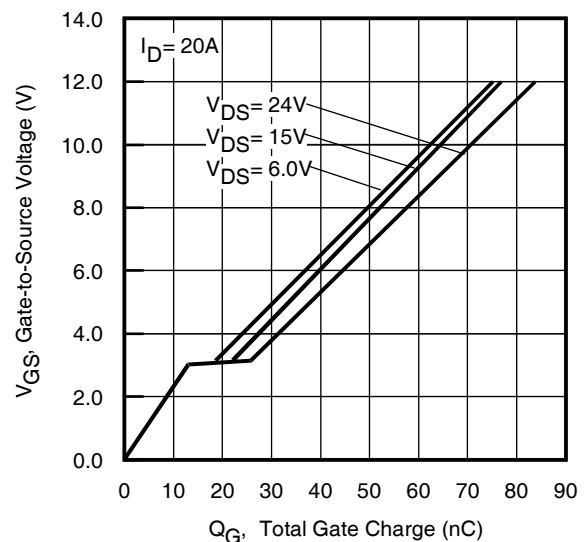
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	326	mJ
I <sub>AR</sub>	Avalanche Current ①	—	20	A

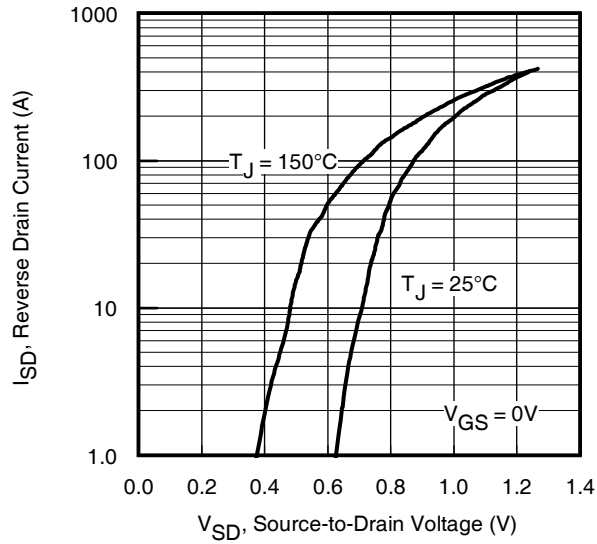
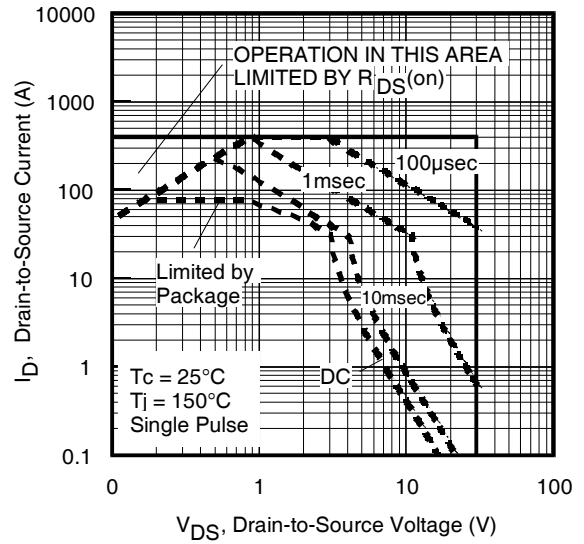
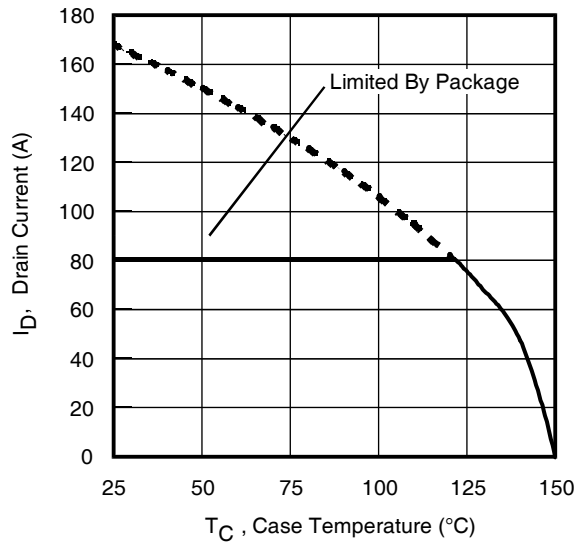
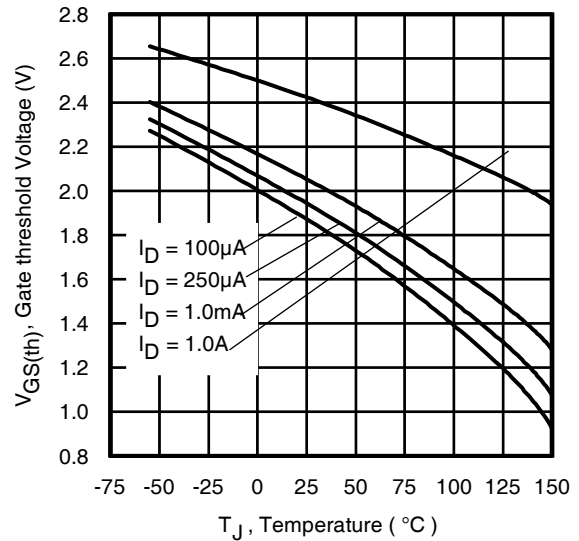
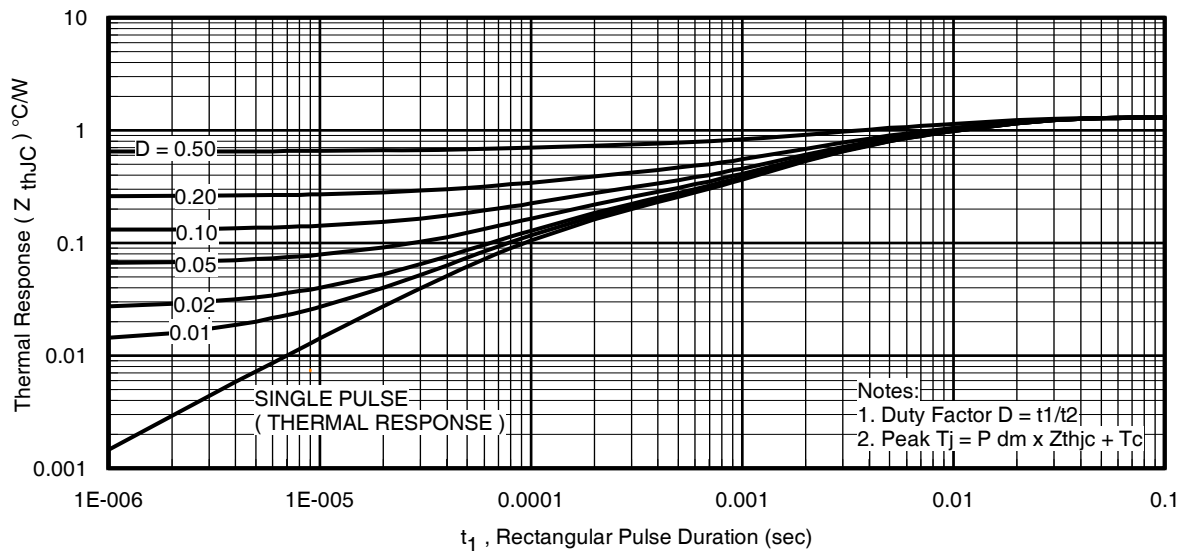
**Diode Characteristics**

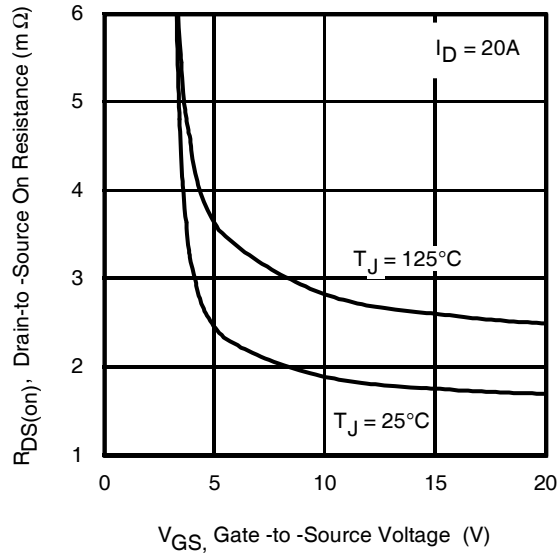
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	80 ②	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	400		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.0	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	22	33	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A, V <sub>DD</sub> = 15V
Q <sub>rr</sub>	Reverse Recovery Charge	—	47	71	nC	di/dt = 390 A/μs ③
t <sub>on</sub>	Forward Turn-On Time	Time is dominated by parasitic Inductance				


**Thermal Resistance**

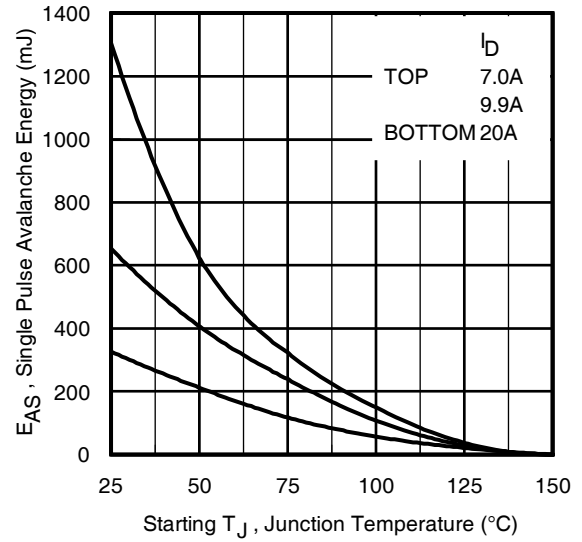
	Parameter	Typ.	Max.	Units
R <sub>θJC</sub> (Bottom)	Junction-to-Case ④	—	1.3	°C/W
R <sub>θJC</sub> (Top)	Junction-to-Case ④	—	30	
R <sub>θJA</sub>	Junction-to-Ambient ⑤	—	35	
R <sub>θJA</sub> (<10s)	Junction-to-Ambient ⑤	—	0.99	


**Fig 1. Typical Output Characteristics**

**Fig 2. Typical Output Characteristics**

**Fig 3. Typical Transfer Characteristics**

**Fig 4. Normalized On-Resistance vs. Temperature**

**Fig 5. Typical Capacitance vs. Drain-to-Source Voltage**

**Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage**

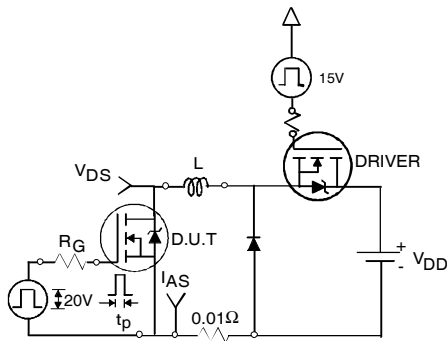

**Fig 7.** Typical Source-Drain Diode Forward Voltage

**Fig 8.** Maximum Safe Operating Area

**Fig 9.** Maximum Drain Current vs. Case (Bottom) Temperature

**Fig 10.** Threshold Voltage vs. Temperature

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case (Bottom)



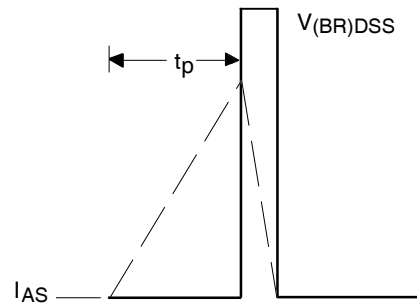
**Fig 12.** On-Resistance vs. Gate Voltage



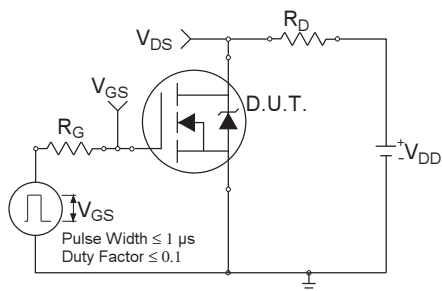
**Fig 13.** Maximum Avalanche Energy vs. Drain Current



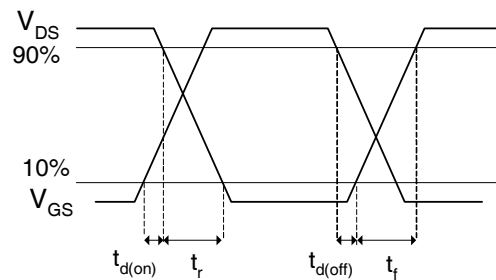
**Fig 14a.** Unclamped Inductive Test Circuit



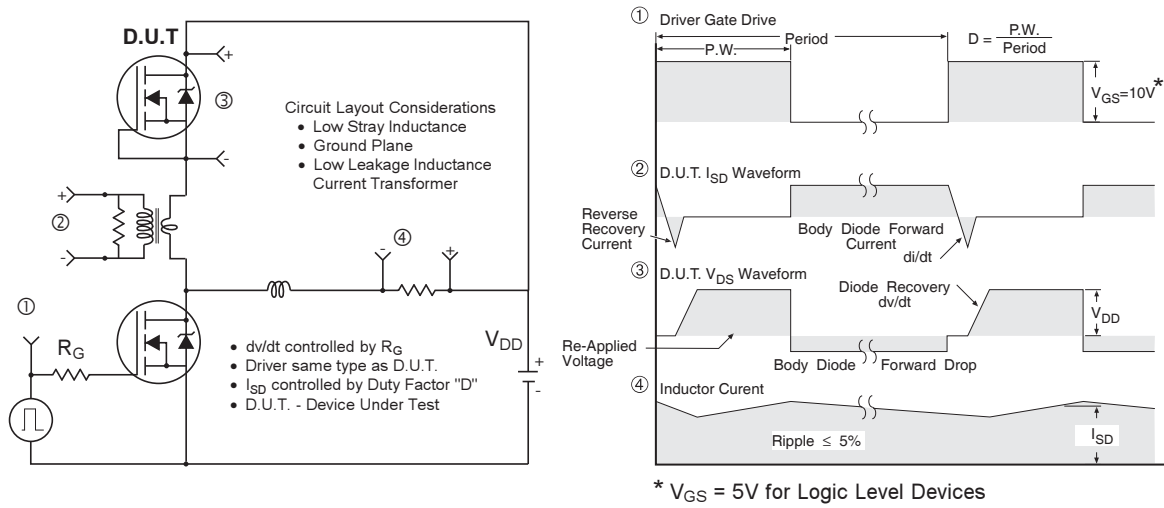
**Fig 14b.** Unclamped Inductive Waveforms



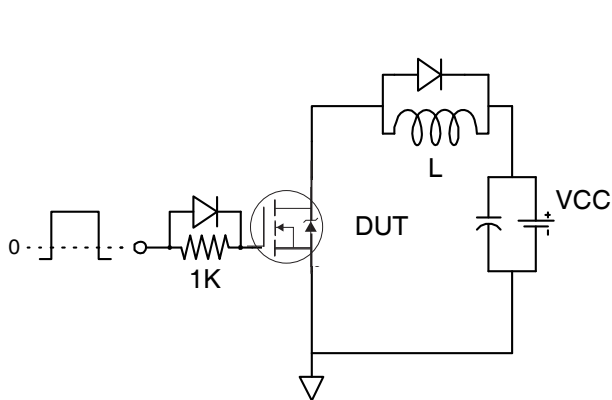
**Fig 15a.** Switching Time Test Circuit



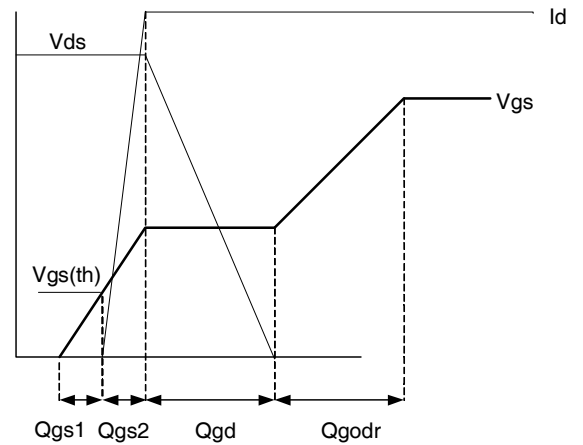
**Fig 15b.** Switching Time Waveforms



**Fig 16. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET<sup>®</sup> Power MOSFETs**

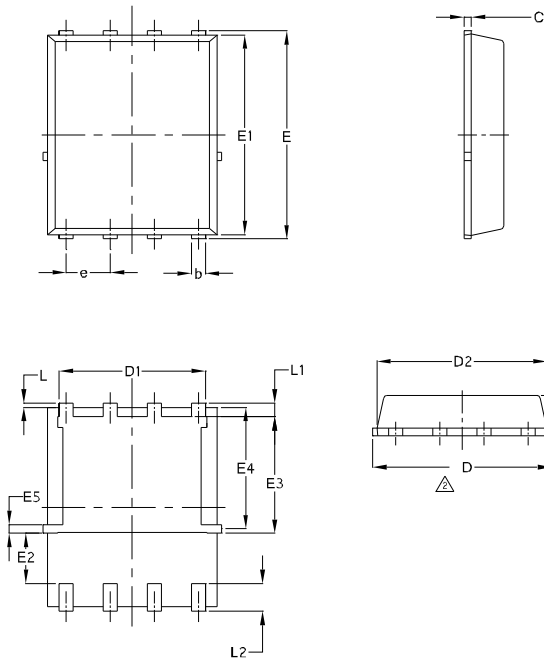


**Fig 17. Gate Charge Test Circuit**



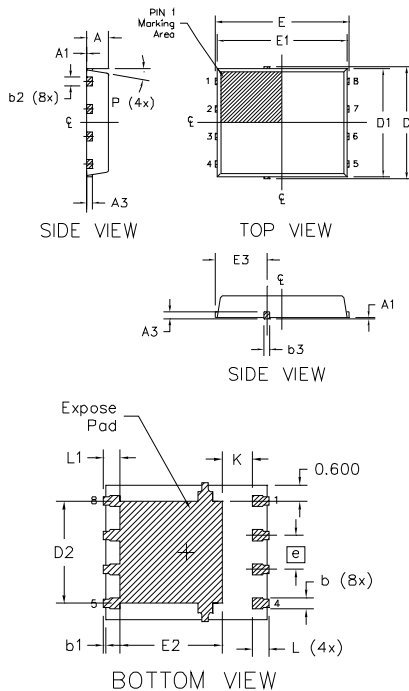
**Fig 18. Gate Charge Waveform**

## PQFN 5x6 Outline "E" Package Details



SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.17	0.0354	0.0461
b	0.33	0.48	0.0130	0.0189
C	0.195	0.300	0.0077	0.0118
D	4.80	5.15	0.1890	0.2028
D1	3.91	4.31	0.1539	0.1697
D2	4.80	5.00	0.1890	0.1968
E	5.90	6.15	0.2323	0.2421
E1	5.65	6.00	0.2224	0.2362
E2	1.51	—	0.0594	—
E3	3.32	3.78	0.1307	0.1480
E4	3.42	3.58	0.1346	0.1409
E5	0.18	0.32	0.0071	0.0126
e	1.27	BSC	0.050	BSC
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.66	0.0150	0.0260
L2	0.51	0.86	0.0201	0.0339
I	0	0.18	0	0.0071

## PQFN 5x6 Outline "G" Package Details



DIM SYMBOL	MILLIMETERS		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.950	1.050	0.0374	0.0413
A1	0.000	0.050	0.0000	0.0020
A3	0.254	REF	0.0100	REF
b	0.310	0.510	0.0122	0.0201
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.180	0.450	0.0071	0.0177
D	5.150	BSC	0.2028	BSC
D1	5.000	BSC	0.1969	BSC
D2	3.700	3.900	0.1457	0.1535
E	6.150	BSC	0.2421	BSC
E1	6.000	BSC	0.2362	BSC
E2	3.560	3.760	0.1402	0.1488
E3	2.270	2.470	0.0894	0.0972
e	1.27	REF	0.050	REF
K	0.830	1.400	0.0327	0.0551
L	0.510	0.710	0.0201	0.0280
L1	0.510	0.710	0.0201	0.0280
P	10 deg	12 deg	0 deg	12 deg

**Notes:**

1. Dimensions and tolerancing conform to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136:

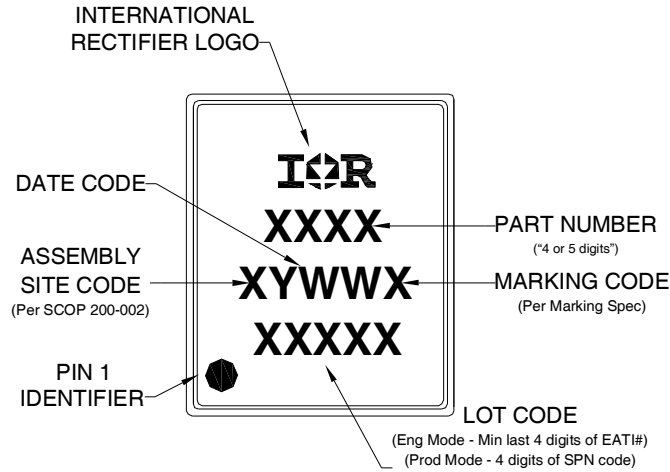
<http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154:

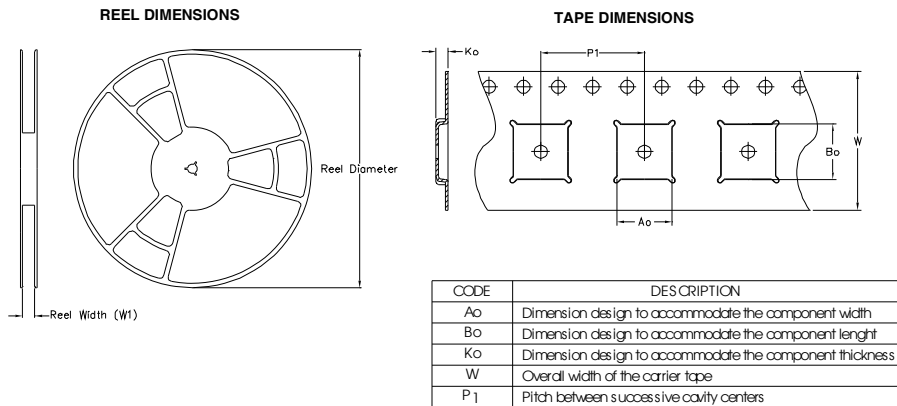
<http://www.irf.com/technical-info/appnotes/an-1154.pdf>

**Note:** For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

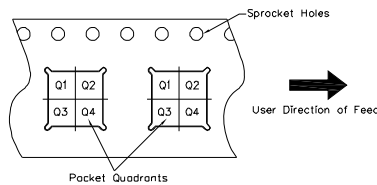
## PQFN 5x6 Part Marking



## PQFN 5x6 Tape and Reel



### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Note: All dimension are nominal

Package Type	Reel Diameter (Inch)	QTY	Reel Width W1 (mm)	Ao (mm)	Bo (mm)	Ko (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
5 X 6 PQFN	13	4000	12.4	6.300	5.300	1.20	8.00	12	Q1

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>



**Qualification information<sup>†</sup>**

Qualification level	Industrial <sup>††</sup> (per JEDEC JE S D47F <sup>†††</sup> guidelines )	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MS L1 (per JEDEC J-STD-020D <sup>†††</sup> )
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier’s web site  
<http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements.  
 Please contact your International Rectifier sales representative for further information:  
<http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^{\circ}\text{C}$ ,  $L = 1.63\text{mH}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 20\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④  $R_{\theta}$  is measured at  $T_J$  of approximately  $90^{\circ}\text{C}$ .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.
- ⑥ Calculated continuous current based on maximum allowable junction temperature.
- ⑦ Current is limited to 80A by source bonding technology.

**Revision History**

Date	Comment
3/26/2010	• Idss limits at $T_J 25^{\circ}\text{C}$ is changed to 500 $\mu\text{A}$ max and at $T_J 125^{\circ}\text{C}$ it is changed to 5.0mA max. All other parameters remain unchanged.
1/7/2014	• Updated ordering information to reflect the End-Of-Life (EOL) of the mini-reel option (EOL notice #259). • Updated data sheet with the new IR corporate template.
6/2/2015	• Updated package outline for “option E” and added package outline for “option G” on page 7. • Updated “IFX” logo on page 1 & 9. • Updated tape and reel on page 8.

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